

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI4401DY-T1-E3

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Si4401DY

Vishay Siliconix

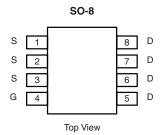
P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 40	0.0155 at $V_{GS} = -10 \text{ V}$	- 10.5		
	0.0225 at V _{GS} = - 4.5 V	- 8.7		

FEATURES

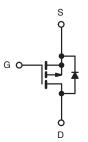
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs





Ordering Information: Si4401DY-T1-E3 (Lead (Pb)-free)

Si4401DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise i	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 40		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Dusin Comment /T 150 °C\2	T _A = 25 °C	- I _D	- 10.5	- 8.7	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 8.3	- 5.9	
Pulsed Drain Current		I _{DM}	- 50		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.7	- 1.36	
	T _A = 25 °C	- P _D	3.0	1.5	w
Maximum Power Dissipation ^a	T _A = 70 °C		1.9	0.95	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian Incation to Austriant	t ≤ 10 s	R _{thJA}	33	42	°C/W
Maximum Junction-to-Ambient ^a	Steady State		70	84	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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Distributor of Vishay/Siliconix: Excellent Integrated System Limited

Datasheet of SI4401DY-T1-E3 - MOSFET P-CH 40V 8.7A 8-SOIC

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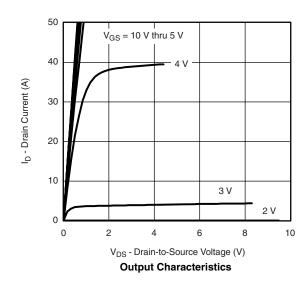
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min. Ty		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1.0			٧	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zava Cata Valtaria Dirain Current	I _{DSS}	V _{DS} = - 32 V, V _{GS} = 0 V	_S = - 32 V, V _{GS} = 0 V		- 1		
Zero Gate Voltage Drain Current		V _{DS} = - 32 V, V _{GS} = 0 V, T _J = 70 °C			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 30			Α	
	В	de 1 B		0.013	0.0155	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}			0.0185	0.0225		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 10.5 A		26		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.7 A, V _{GS} = 0 V		- 0.74	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Q_g			37.5	50	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -10.5 \text{ A}$		14.3			
Gate-Drain Charge	Q_{gd}			10.7			
Turn-On Delay Time	t _{d(on)}			17	30		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		18	30	ns	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 10 V, R_g = 6 Ω		122	190		
Fall Time	t _f			55	85		
Gate Resistance	R_g			3.8		Ω	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dI/dt = 100 A/μs		45		ns	

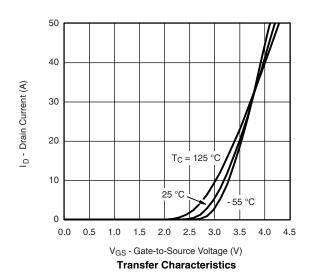
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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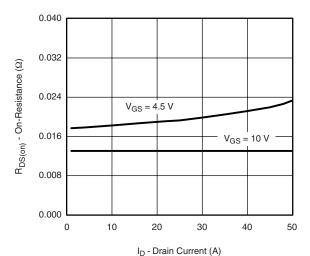




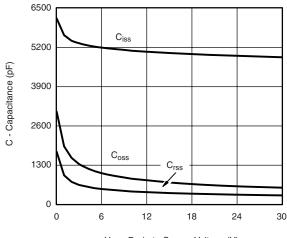
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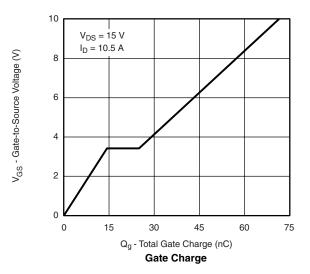


On-Resistance vs. Drain Current

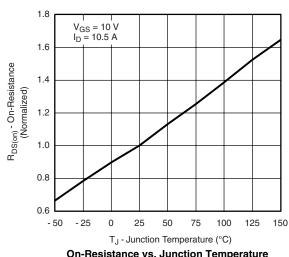


V_{DS} - Drain-to-Source Voltage (V)

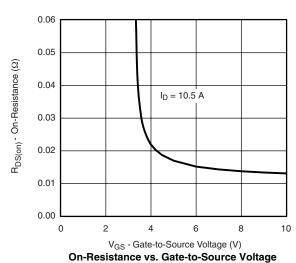




50 Is - Source Current (A) T_{.1} = 150 °C 10 $T_J = 25$ °C 0.0 1.0 1.2 V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage



On-Resistance vs. Junction Temperature



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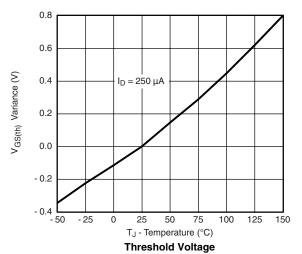


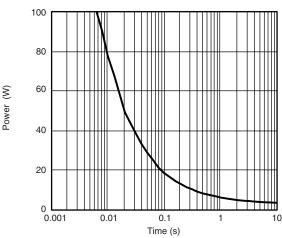
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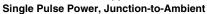
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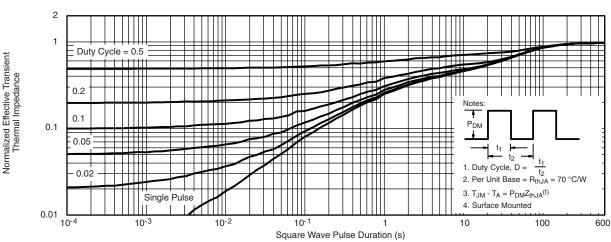
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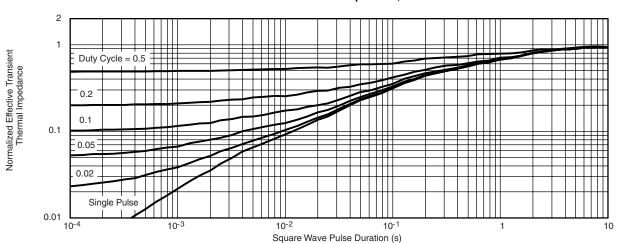








Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71226.



Distributor of Vishay/Siliconix: Excellent Integrated System Limited

Datasheet of SI4401DY-T1-E3 - MOSFET P-CH 40V 8.7A 8-SOIC

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